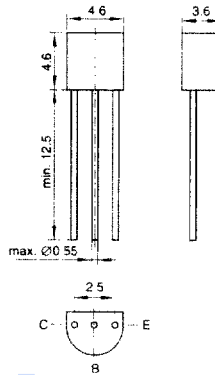


PNP Silicon Epitaxial Planar Transistors

for switching and amplifier applications. Especially suitable for AF-driver stages and low-power output stages.

These types are also available subdivided into three groups -16, -25, and -40, according to their DC current gain. As complementary types, the NPN transistors BC337 and BC338 are recommended.

On special request, these transistors are also manufactured in the pin configuration TO-18.



TO-92 Plastic Package
 Weight approx. 0.18 g
 Dimensions in mm

Datasheet.Live

Absolute Maximum Ratings

		Symbol	Value	Unit
Collector-Emitter Voltage	BC327	$-V_{CES}$	50	V
	BC328	$-V_{CES}$	30	V
Collector-Emitter Voltage	BC327	$-V_{CEO}$	45	V
	BC328	$-V_{CEO}$	25	V
Emitter-Base Voltage		$-V_{EBO}$	5	V
Collector Current		$-I_C$	800	mA
Peak Collector Current		$-I_{CM}$	1	A
Base Current		$-I_B$	100	mA
Power Dissipation at $T_{amb} = 25\text{ }^\circ\text{C}$		P_{tot}	625 ¹⁾	mW
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature Range		T_S	-65... +150	$^\circ\text{C}$

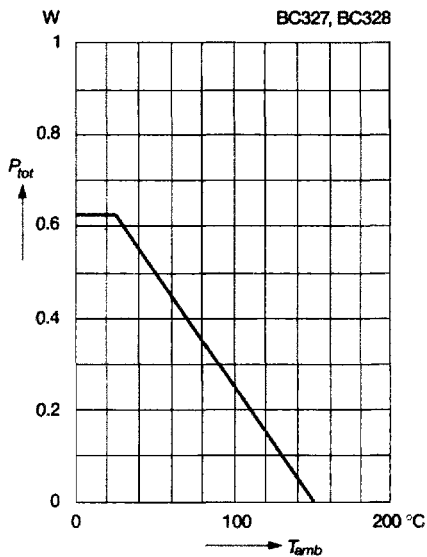
¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

Characteristics at $T_{amb} = 25\text{ }^{\circ}\text{C}$

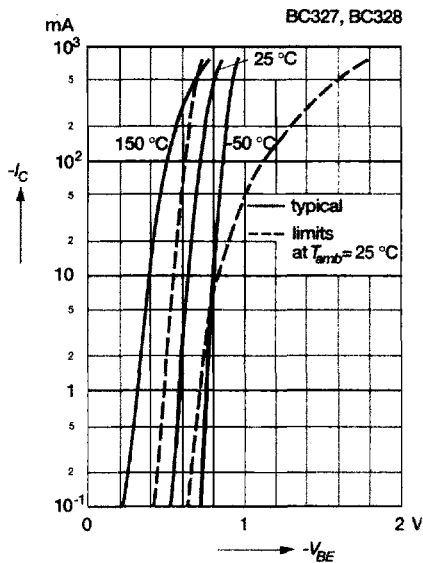
	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$					
Current Gain Group-16	h_{FE}	100	160	250	-
-25	h_{FE}	160	250	400	-
-40	h_{FE}	250	400	630	-
at $-V_{CE} = 1\text{ V}$, $-I_C = 300\text{ mA}$					
Current Gain Group-16	h_{FE}	60	130	-	-
-25	h_{FE}	100	200	-	-
-40	h_{FE}	170	320	-	-
Thermal Resistance Junction to Ambient Air	R_{thA}	-	-	200 ¹⁾	K/W
Collector-Emitter Cutoff Current at $-V_{CE} = 45\text{ V}$	BC327				
at $-V_{CE} = 25\text{ V}$	BC328				
at $-V_{CE} = 45\text{ V}$, $T_{amb} = 125\text{ }^{\circ}\text{C}$	BC327				
at $-V_{CE} = 25\text{ V}$, $T_{amb} = 125\text{ }^{\circ}\text{C}$	BC328				
	$-I_{CES}$	-	2	100	nA
	$-I_{CES}$	-	2	100	nA
	$-I_{CES}$	-	-	10	μA
	$-I_{CES}$	-	-	10	μA
Collector-Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	BC327				
	BC328				
	$-V_{(BR)CEO}$	45	-	-	V
	$-V_{(BR)CEO}$	25	-	-	V
Collector-Emitter Breakdown Voltage at $-I_C = 0.1\text{ mA}$	BC327				
	BC328				
	$-V_{(BR)CES}$	50	-	-	V
	$-V_{(BR)CES}$	30	-	-	V
Emitter-Base Breakdown Voltage at $-I_E = 0.1\text{ mA}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{CEsat}$	-	-	0.7	V
Base-Emitter Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 300\text{ mA}$	$-V_{BE}$	-	-	1.2	V
Gain-Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 50\text{ MHz}$	f_T	-	100	-	MHz
Collector-Base Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{CBO}	-	12	-	pF
1) Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.					

Admissible power dissipation versus ambient temperature

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

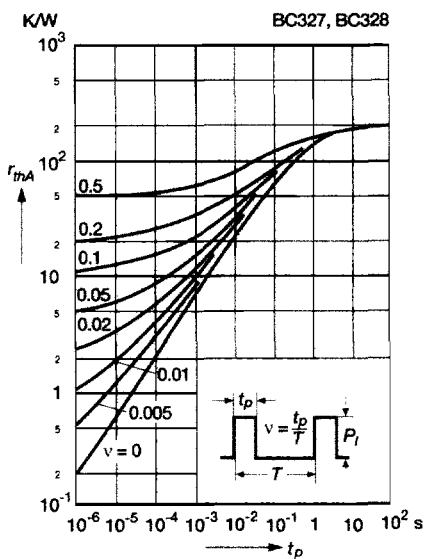


Collector current versus base-emitter voltage

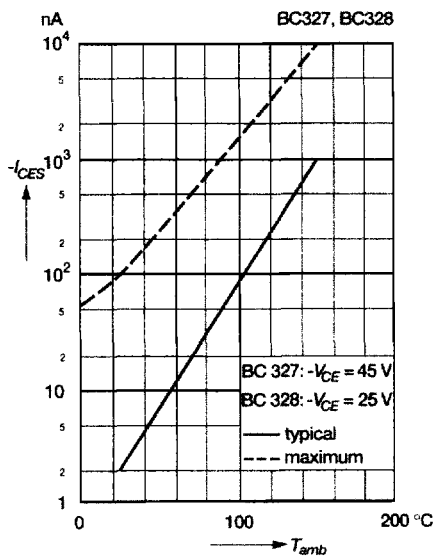


Pulse thermal resistance versus pulse duration

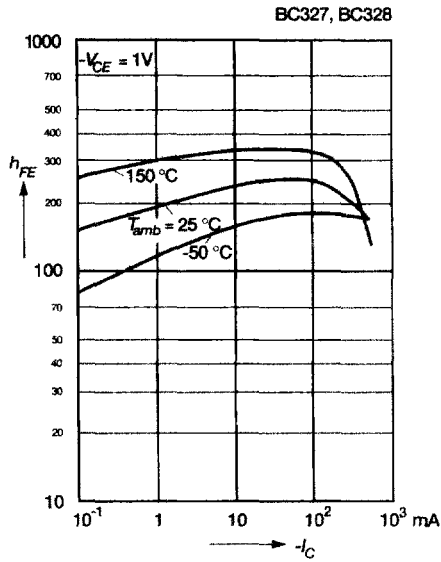
Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



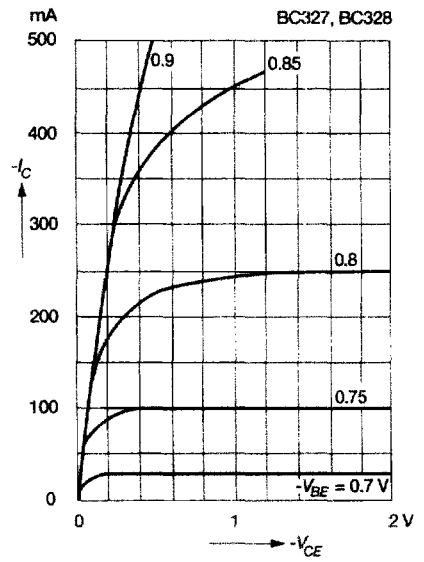
Collector-emitter cutoff current versus ambient temperature



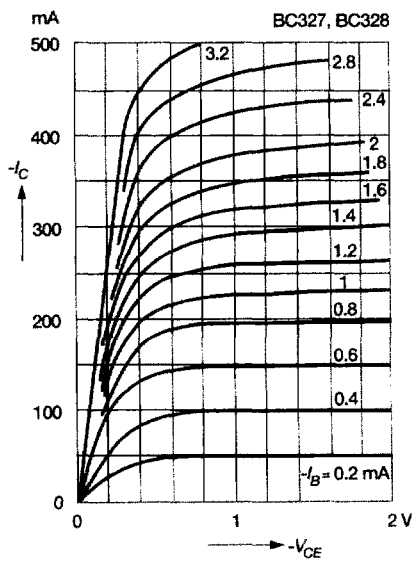
DC current gain versus collector current



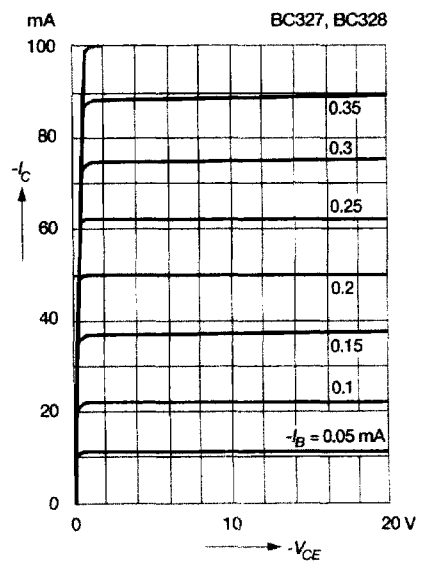
Common emitter collector characteristics



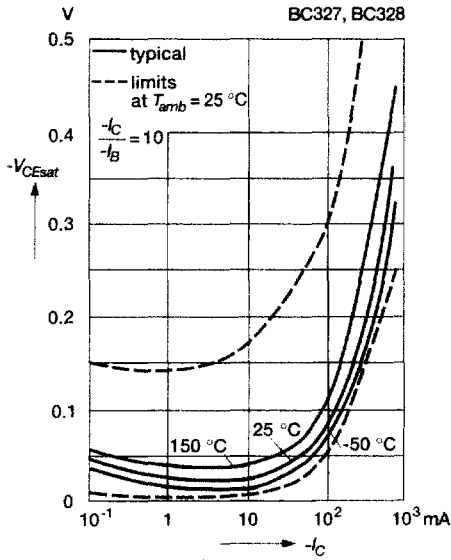
Common emitter collector characteristics



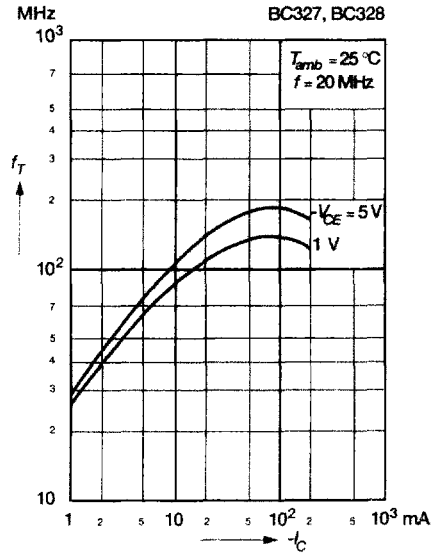
Common emitter collector characteristics



Collector saturation voltage versus collector current



Gain-bandwidth product versus collector current



Base saturation voltage versus collector current

